



	Experiment title: Anomalous GISAXS of a solution-processed oxide semiconductor as a function of thermal annealings	Experiment number: 02-01-842
Beamline: BM02	Date of experiment: from: 05 sept. 2013 to: 08 sept. 2013	Date of report: 12/01/2016
Shifts: 9	Local contact(s): Mireille Maret	<i>Received at ESRF:</i>
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Report:**Abstract:**

Self-organized nanoclusters were obtained in annealed solution-processed In–Ga–Zn–O thin films. STEM and anomalous grazing incidence small-angle X-ray scattering (GISAXS) reveal the formation of nanometer-sized nanoclusters together with the spontaneous creation of a mesopore pattern.

Publication:

Self-organized nanoclusters in solution-processed mesoporous In–Ga–Zn–O thin films,
C. Revenant, M. Benwadih and M. Maret
Chem. Commun., 2015, **51**, 1218-1221.